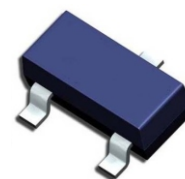


General Purpose Transistor

COMCHIP

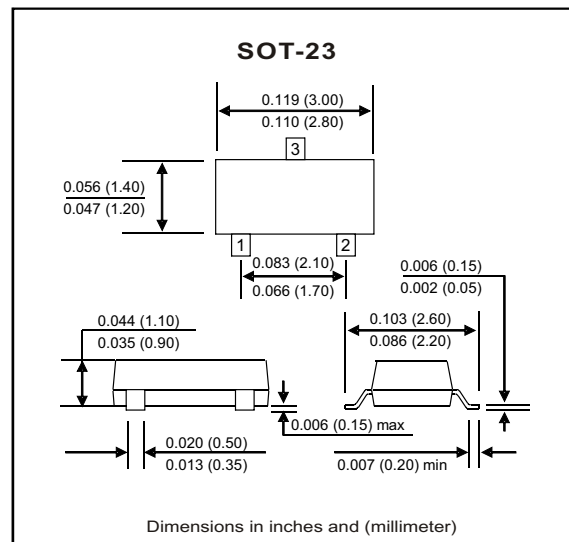
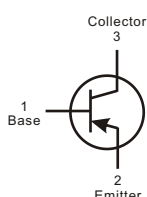
SMD Diodes Specialist

MMBT2907-G (PNP) RoHS Device



Features

- Epitaxial planar die construction
- Device is designed as a general purpose amplifier and switching.



Maximum Ratings(at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Min	Max	Unit
Collector-Base voltage	V_{CB0}		-60	V
Power dissipation	P_{CM}		0.3	W
Collector current-Continuous	I_{CM}		-0.6	A
Storage temperature and junction temperature	T_{STG}, T_J	-55	+150	$^{\circ}\text{C}$

Electrical Characteristics(at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Max	Unit
Collector-Base breakdown voltage	$I_C=-10\mu\text{A}, I_E=0$	$V_{(BR)CBO}$	-60		V
Collector-emitter breakdown voltage	$I_C=-10\text{mA}, I_B=0$	$V_{(BR)CEO}$	-40		V
Emitter-base breakdown voltage	$I_E=-10\mu\text{A}, I_C=0$	$V_{(BR)EBO}$	-5		V
Collector cut-off current	$V_{CB}=-50\text{V}, I_E=0$	I_{CBO}		-0.1	μA
Collector cut-off current	$V_{CB}=-35\text{V}, I_B=0$	I_{CEO}		-0.1	μA
Emitter cut-off current	$V_{EB}=-3\text{V}, I_C=0$	I_{EBO}		-0.1	μA
DC current gain	$V_{CE}=-10\text{V}, I_C=-150\text{mA}$	$h_{FE(1)}$	100	300	
	$V_{CE}=-10\text{V}, I_C=-1\text{mA}$	$h_{FE(2)}$	50		
Collector-emitter saturation voltage	$I_C=-500\text{mA}, I_B=-50\text{mA}$	$V_{CE(sat)}$		-1	V
Base-emitter saturation voltage	$I_C=-500\text{mA}, I_B=-50\text{mA}$	$V_{BE(sat)}$		-2	V
Transition frequency	$V_{CE}=-20\text{V}, I_C=-50\text{mA}$ $F=100\text{MHz}$	f_T	200		Mhz

REV:A